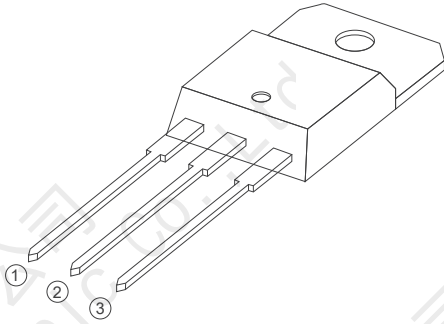


TYN1225 Series

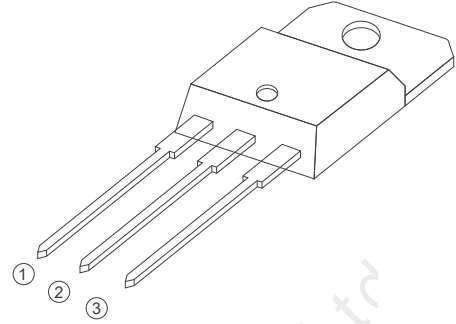
25A SCRs



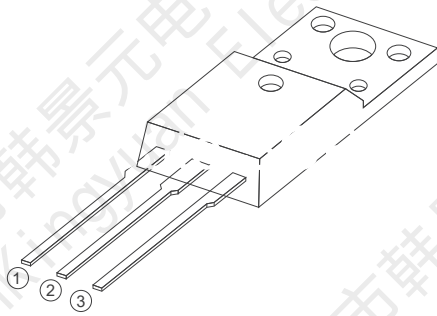
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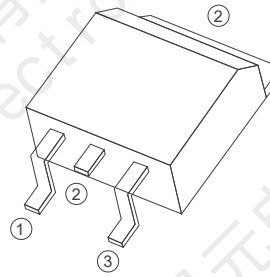
TO-220A Insulated



TO-220B Non-Insulated



TO-220F Insulated



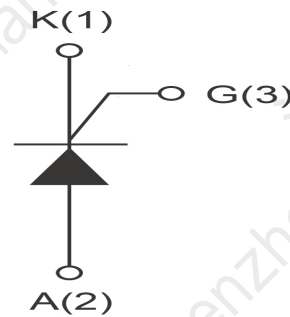
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FEATURES

> $I_T(RMS): 25A$ > $V_{GT}: 1.5V$ > $V_{DRM} V_{RRM}: 1200 \sim 1600V$

APPLICATIONS

Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.



Absolute Maximum Ratings (T_j=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
VDRM VRRM	Repetitive Peak Off-State Voltage	TYN1225	1200	V
		TYN1625	1600	
IT(RMS)	R.M.S On-State Current		25	A
ITSM	Surge On-State Current	F=50Hz, tp=10ms	250	A
I ² t	I ² t for fusing	tp=10ms	310	A ² s
IGM	Peak Gate Current	tp=20us T _j =110°C	1.5	A
PG(AV)	Average Gate Power Dissipation	T _j =125°C	2	W
PGM	Peak Gate Current	T _j =125°C	5	W
T _j	Operating Junction Temperature		~40~125	°C
TSTG	Storage Temperature		~40~150	°C

Electrical Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Value	Unit
IDRM	Repetitive Peak Off-State Current	T _c =25°C	≤10	uA
		T _c =125°C	≤4	mA
IRRM	Repetitive Peak Reverse Current	T _c =25°C	≤10	uA
		T _c =125°C	≤4	mA
VTM	Forward "on" voltage	IT=50A tp=380us	≤1.55	V
VGD	Gate nontrigger voltage	VD=VDRM, T _j =125°C, RL=3.3KΩ	≥0.25	V
IL	Latching current	IG=1.2IGT	≤150	mA
IH	Holding current	VD=12V, IGT=0.1A	≤120	mA
VGT	Gate trigger voltage	VD=12V	≤1.3	V
IGT	Gate trigger current	VD=12V, IT=0.1A	≤35	mA
dv/dt	Critical-rate of rise of commutation voltage	VD=2/3VDRM, T _j =110°C, RGK=1KΩ	≥1000	V/us
di/dt	Critical-rate of rise of commutation current	IG=2XIG, tr≤100us, T _j =125°C	≥100	A/us
Rth(j-c)	Thermal resistance	Junction to case	2.1	°C/W

FIG1

Maximum power dissipation versus RMS on-state current

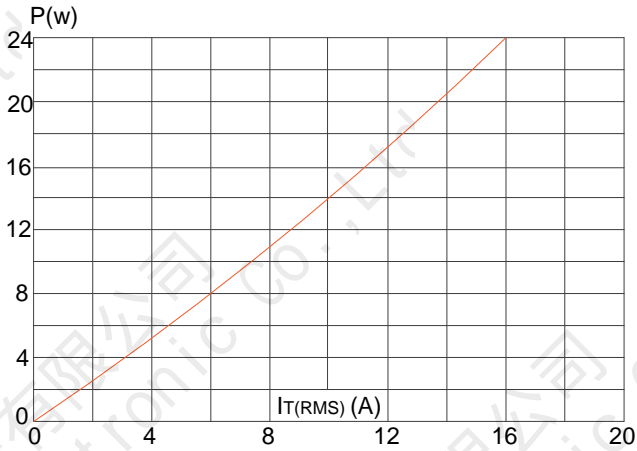


FIG2

RMS on-state current versus case temperature

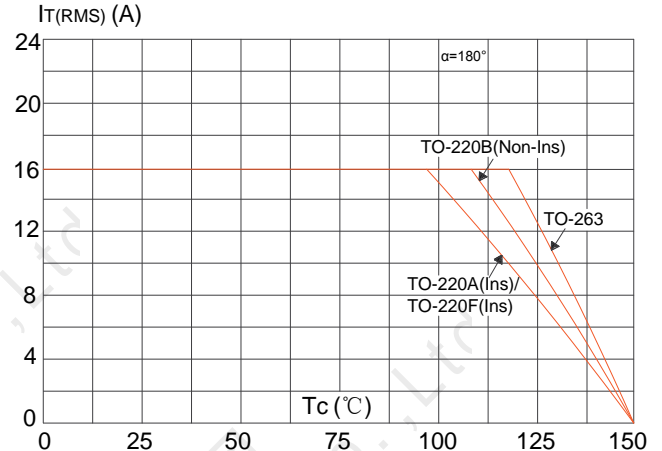


FIG3

Surge peak on-state current versus number of cycles

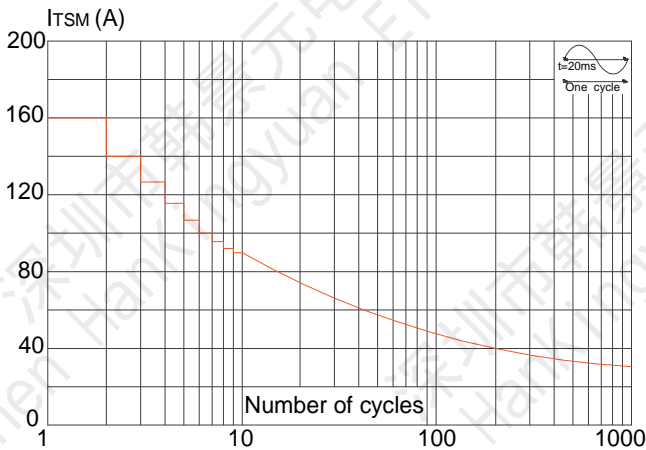


FIG4

On-state characteristics (maximum values)

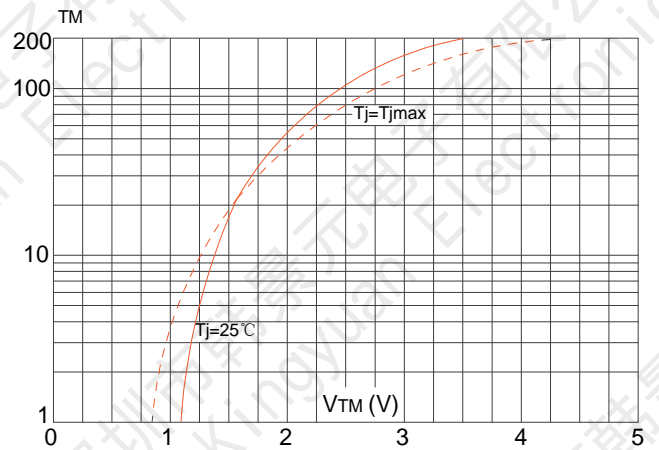


FIG5

Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

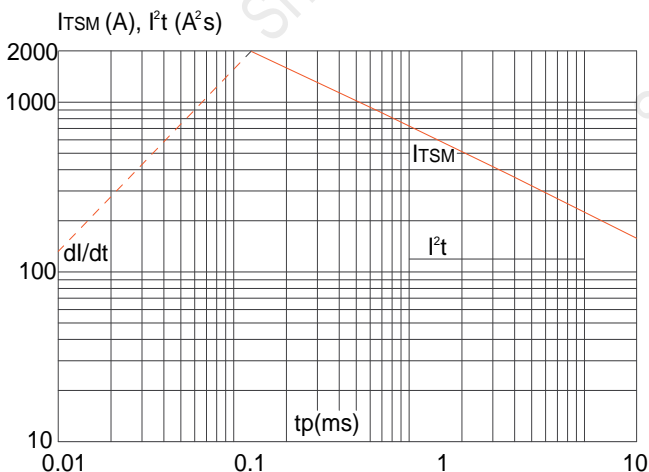
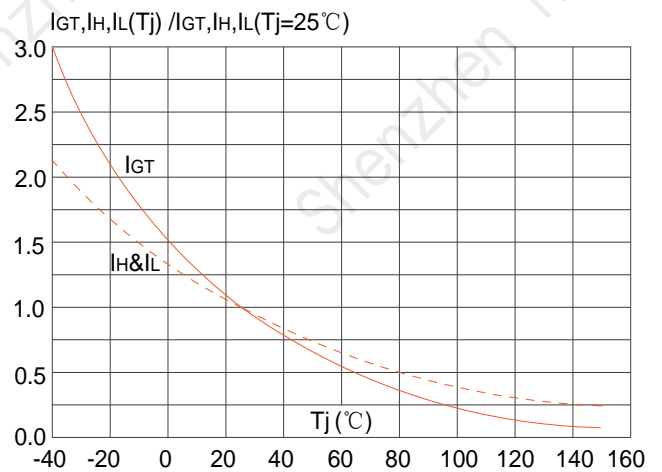
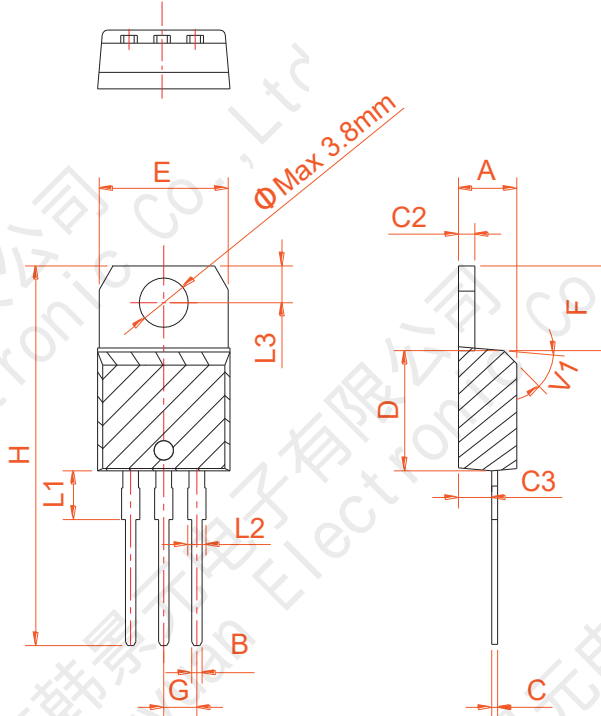


FIG6

Relative variations of gate trigger current, holding current and latching current versus junction temperature



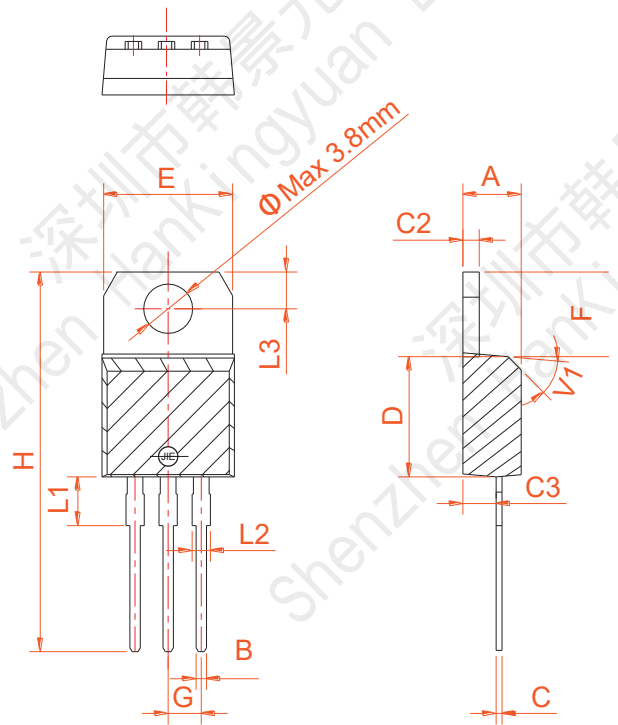
PACKAGE MECHANICAL DATA



TO-220A Ins

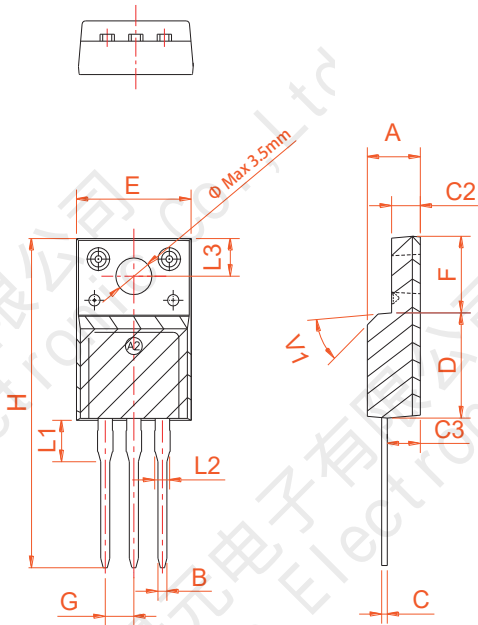
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220B Non-Ins

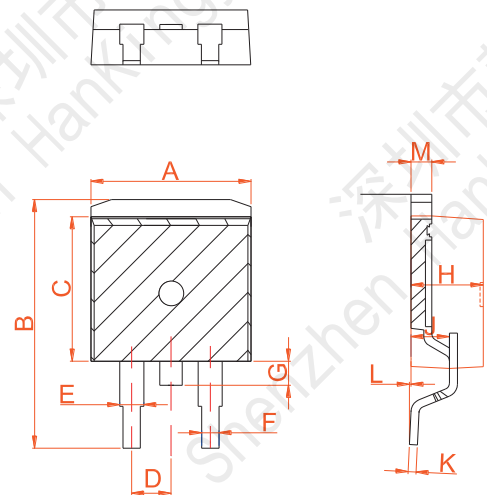
PACKAGE MECHANICAL DATA



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053



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